



Attorney Docket No. FUJ 99228 CIP
Client Matter. No. 80458.0004.001

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Katsuyoshi MATSUURA, et al.

Serial No. 09/551,233

Filed: April 17, 2000

Title: SEMICONDUCTOR DEVICE HAVING A
FERROELECTRIC CAPACITOR AND A
FABRICATION PROCESS THEREOF

Examiner: H.-M. Lee
Art Unit: 2823

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Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

The undersigned hereby certifies that the attached:

1. Amendment & Response to Second Office Action;
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AMENDMENT & RESPONSE TO SECOND OFFICE ACTION

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed August 22, 2001 for which a shortened statutory period for response was set to November 22, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claim 20.

Please amend claims 1, 15, 16, 19 and 21 as follows:

1. (Twice Amended) A method of fabricating a semiconductor device having a ferroelectric capacitor, comprising the steps of:

forming an active device element on a substrate;

forming an insulation film over said substrate to cover said active device element;

forming a lower electrode layer of said ferroelectric capacitor over said insulation film;

forming a PZT ferroelectric film on said lower electrode layer as a capacitor insulation film of said ferroelectric capacitor;